

# Study and characterisation of high-quantum-efficiency photocathodes for high brightness photo injectors

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Supervisor: Dott. Massimo Ferrario  
On behalf of SPARC\_LAB collaboration

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- Motivation
- Background
- Surface Analysis Techniques
  - Scanning Electron Microscopy with Energy Dispersive Spectroscopy (*SEM-EDS*)
  - Atomic Force Microscopy (*AFM*)
- Machining and Results
- Fourier transform of AFM images and surface roughness induced emittance
- Emittance measurements
- Preliminary study of Yttrium photocathodes
- Conclusions

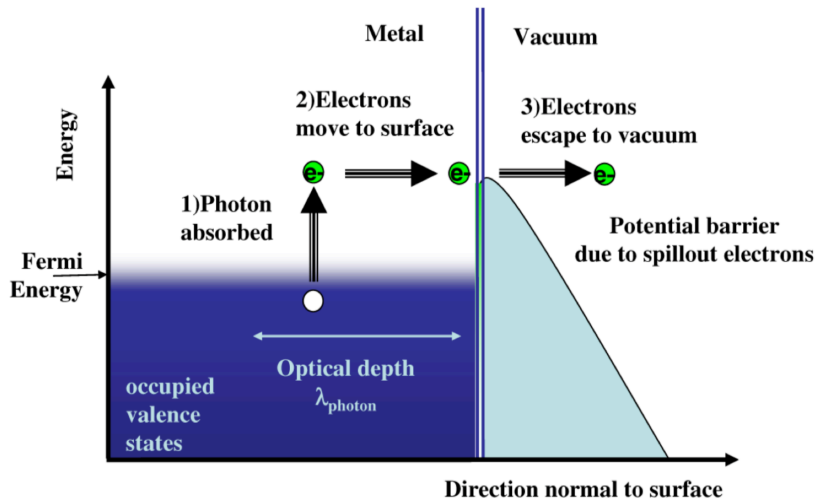
- **High brightness** (high current, **low emittance**) **electron beam** production by photoinjector at SPARC\_LAB
- A **R&D activity** on photocathodes is under development at the SPARC\_LAB test facility in order to fully know and characterize each stage of the photocathode “life”
- The **n-machining** is used to reduce roughness, that is one of contributions to the total beam emittance, and avoid surface contamination caused by other procedures, for example the polishing with diamond paste or the machining with oil

## ➤ ELECTRON EMISSION PROCESS OF METALLIC PHOTOCATHODES AND THE 3-STEP MODEL

Photoelectric emission from a metal given by Spicer's 3-step model:

1. Photon absorption by the electron
2. Electron transport to the surface
3. Escape through the barrier

QE and emittance depend upon electronic structure of the cathode



The *Quantum Efficiency (QE)* is:

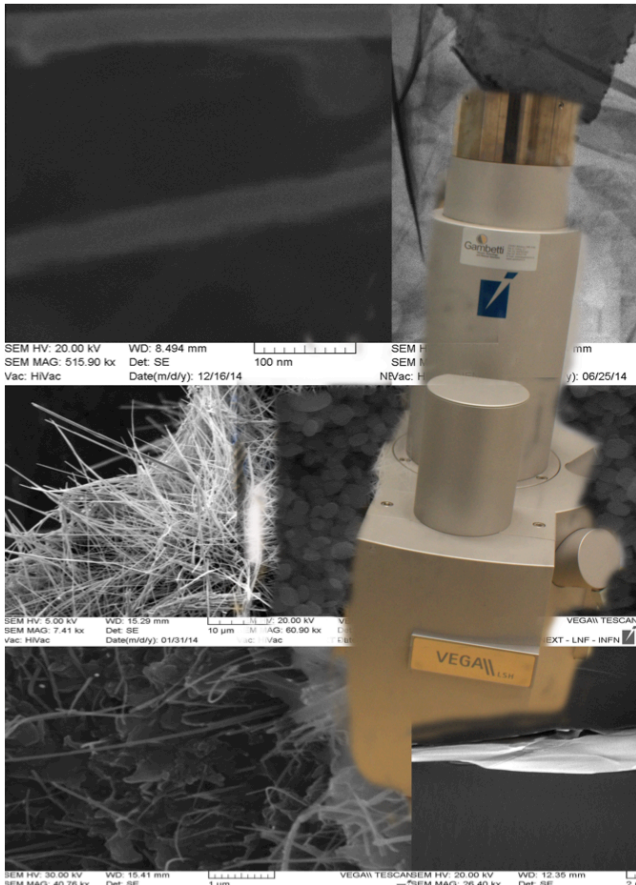
$$QE = \frac{n_e}{n_p} = \frac{h\nu [eV]}{E_{\text{laser}} [J]} q [C]$$

The *thermal emittance ( $\epsilon_{th}$ )* is:

$$\epsilon_{th} = \sigma_x \sigma_{p_x} = \sigma_x \sqrt{\frac{\hbar\omega - \phi_{eff}}{3mc^2}}$$

The electric potential energy is:

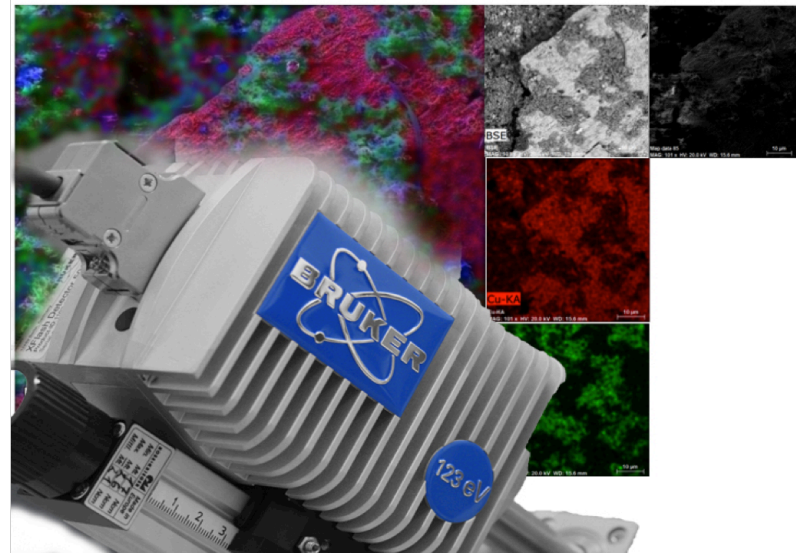
$$e\phi_{eff} = e\phi_{work} - \frac{e^2}{16\pi\epsilon_0 x} - eE_0 x$$



The types of signals produced by a **SEM** include:

- secondary electrons (**SE**), emitted from very close to the sample surface (**morphology**);
- back scattered electrons (**BSE**): electrons beam that are reflected from the sample by elastic scattering (**atomic number, Z**).

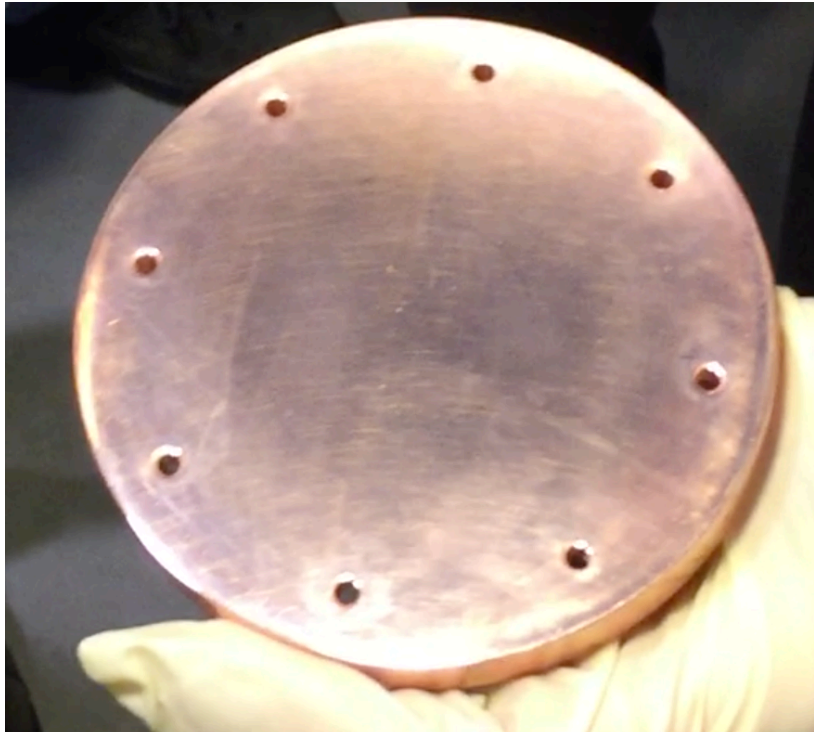
➤ We are able to determine the chemical composition of the test sample with the **Energy Dispersive Spectroscopy (EDS)**.



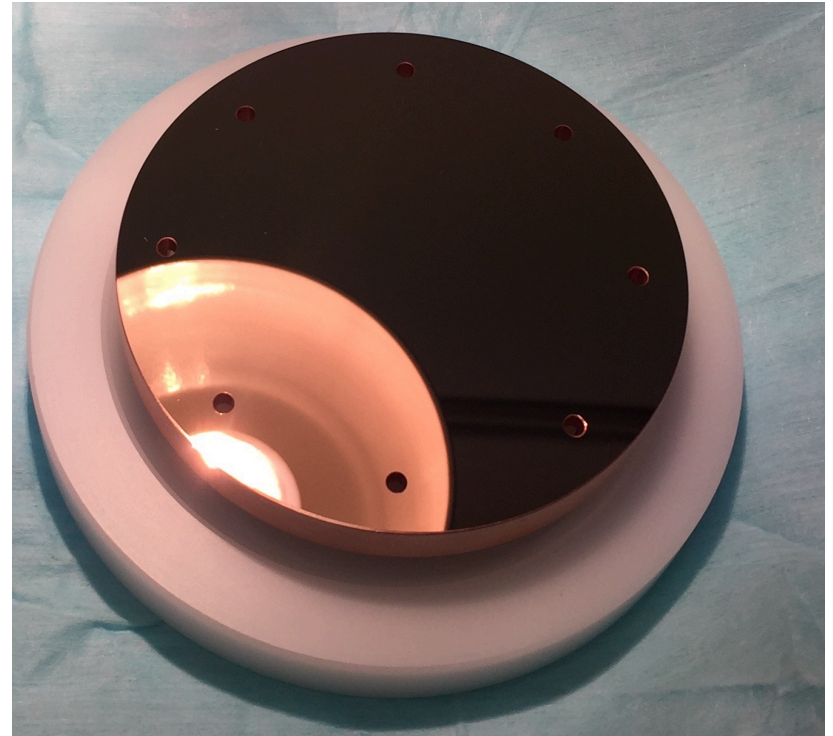
- The photocathode surface has been machined by means of diamond milling and blown with nitrogen. The machining has been done without the use of any oil or cooling fluid (dry machining).

## BEFORE MACHINING

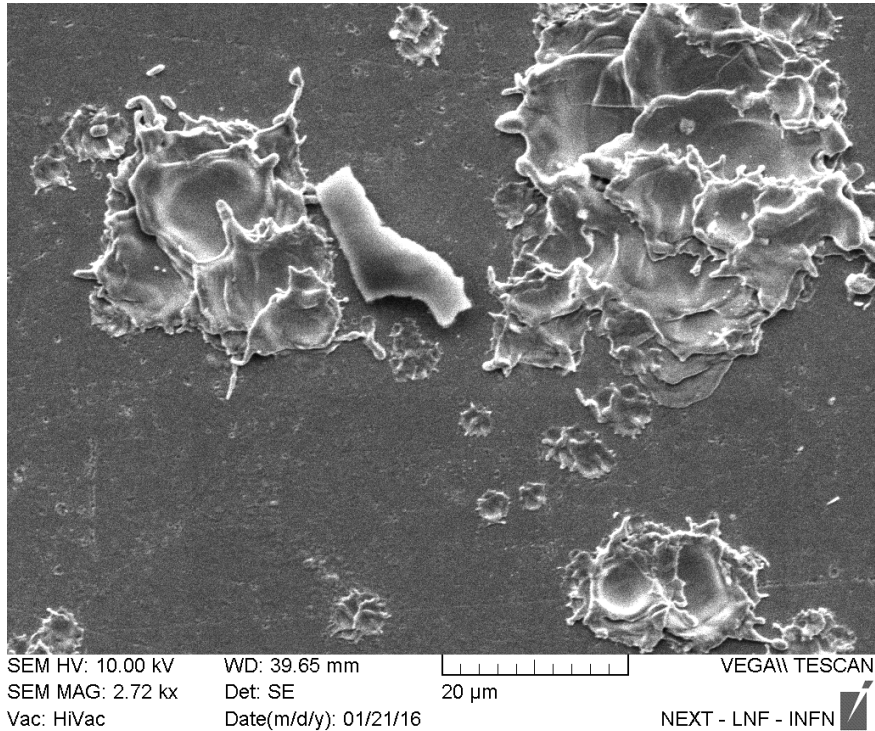
*Our cathode time life was about 6 years*



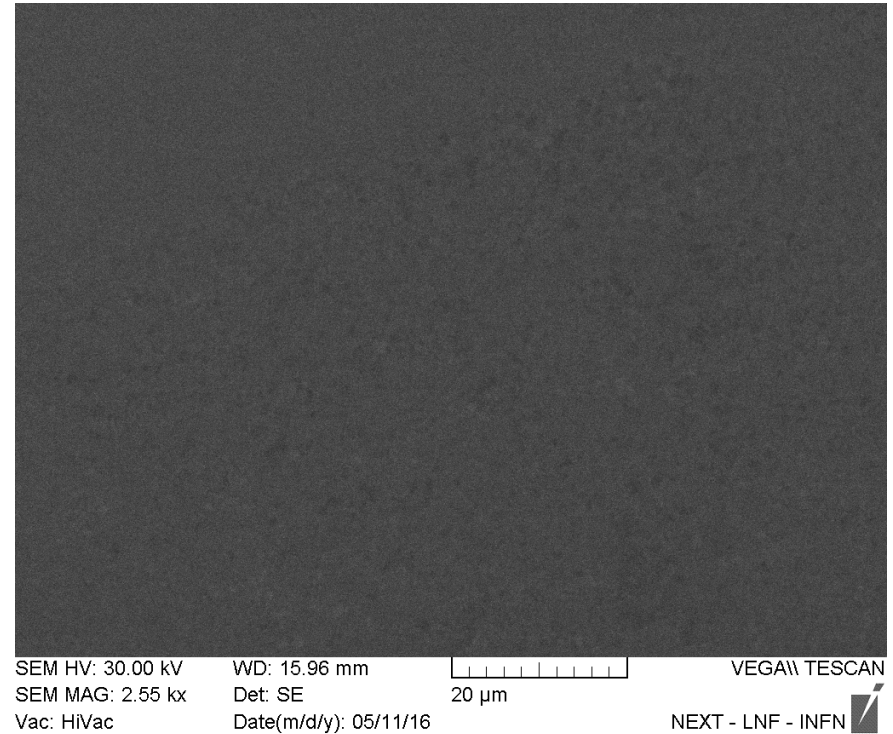
## AFTER MACHINING



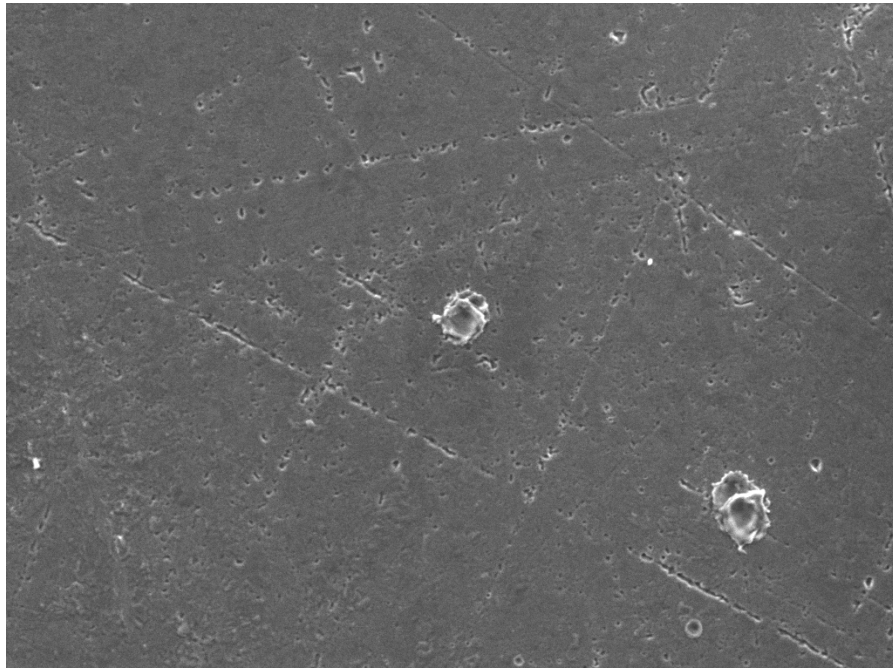
## BEFORE MACHINING

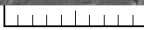



## AFTER MACHINING

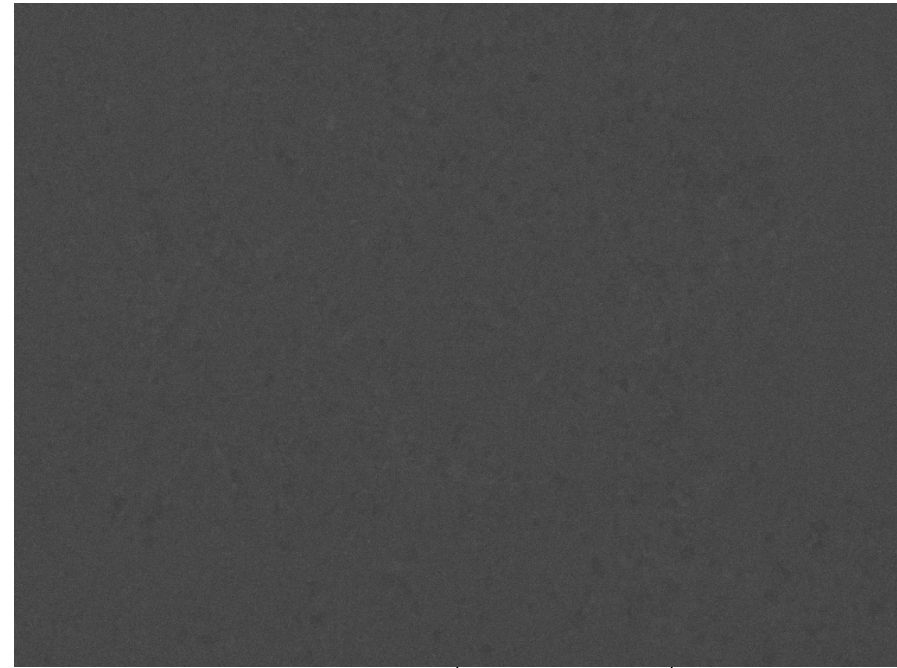


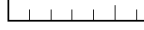

## BEFORE MACHINING



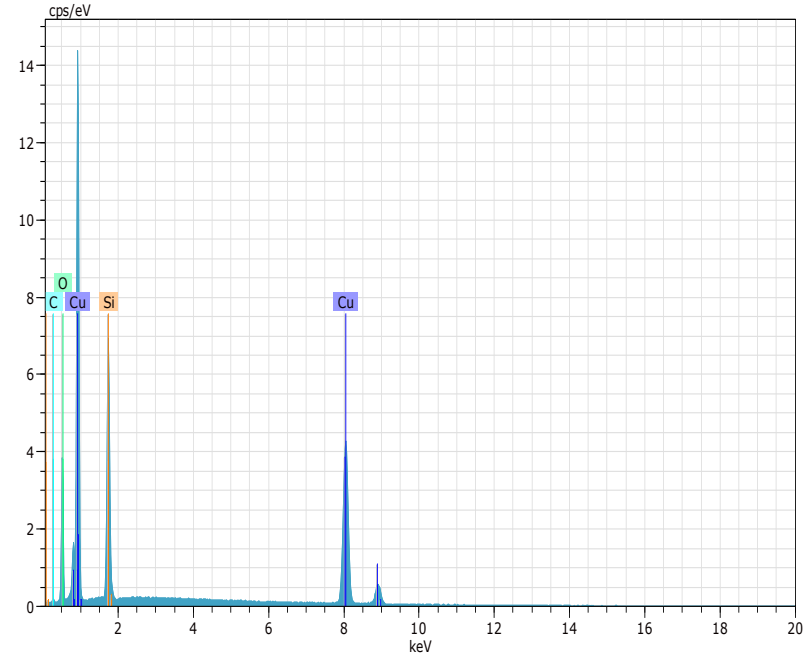
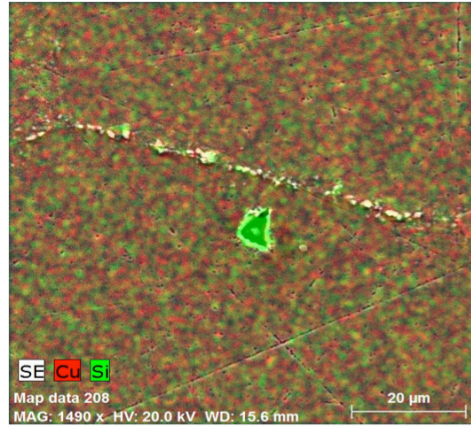
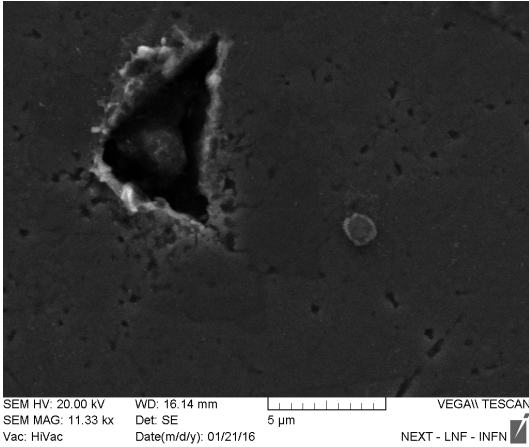
SEM HV: 10.00 kV    WD: 39.65 mm        VEGA\\ TESCAN  
 SEM MAG: 4.07 kx    Det: SE  
 Vac: HiVac    Date(m/d/y): 01/21/16    NEXT - LNF - INFN 

## AFTER MACHINING



SEM HV: 30.00 kV    WD: 15.91 mm        VEGA\\ TESCAN  
 SEM MAG: 6.14 kx    Det: SE  
 Vac: HiVac    Date(m/d/y): 05/11/16    NEXT - LNF - INFN 

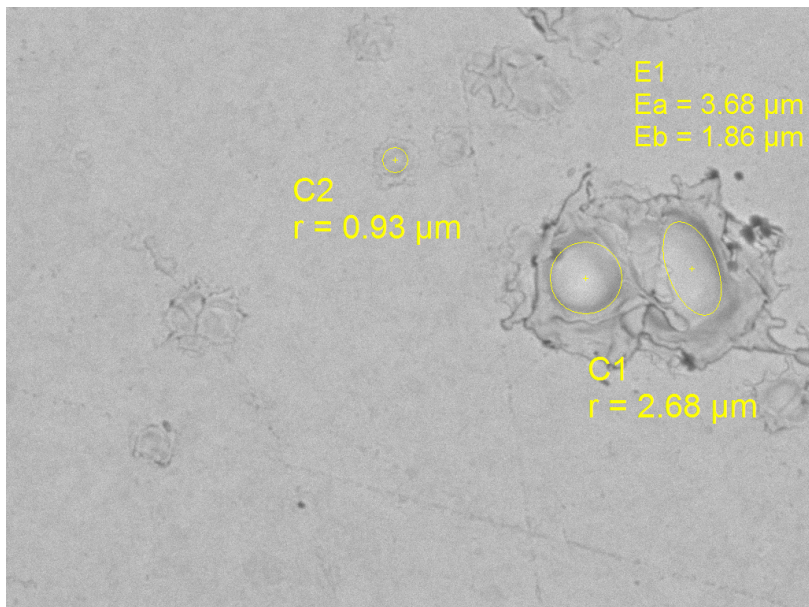




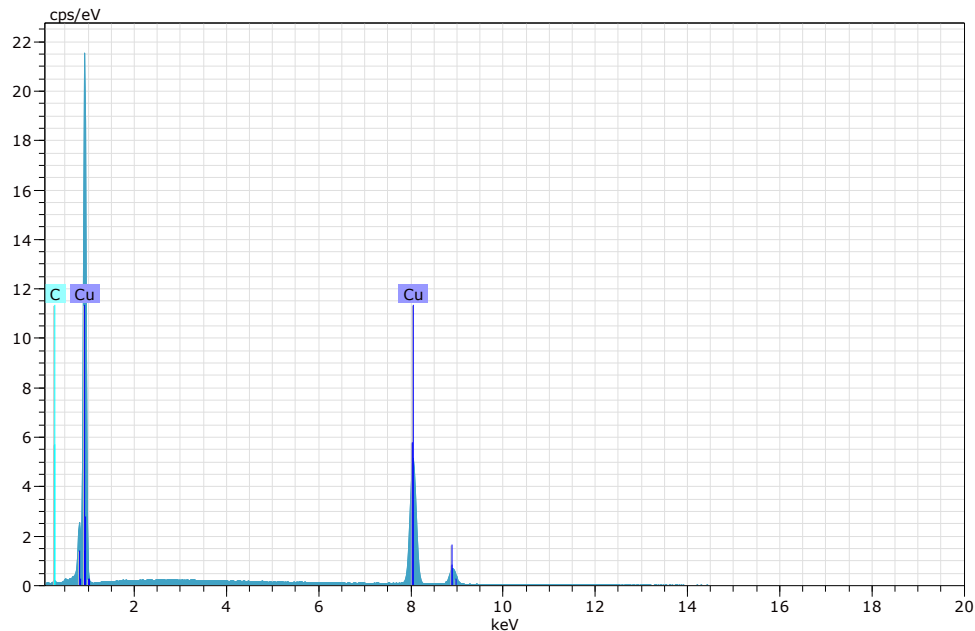
Spectrum: Acquisition 862 - particella.spx

El AN Series unn. C norm. C Atom. C Error (1 Sigma) K fact. Z corr. A corr. F corr.  
 [wt.%) [wt.%) [at.%) [wt.%)

|        |    |          |       |        |        |      |       |       |       |       |
|--------|----|----------|-------|--------|--------|------|-------|-------|-------|-------|
| Cu     | 29 | K-series | 62.20 | 63.79  | 34.62  | 1.72 | 0.548 | 1.114 | 1.000 | 1.044 |
| O      | 8  | K-series | 17.08 | 17.51  | 37.76  | 2.31 | 0.377 | 0.464 | 1.000 | 1.000 |
| Si     | 14 | K-series | 15.46 | 15.86  | 19.47  | 0.69 | 0.131 | 1.203 | 1.000 | 1.004 |
| C      | 6  | K-series | 2.77  | 2.84   | 8.15   | 0.76 | 0.077 | 0.369 | 1.000 | 1.000 |
| Total: |    |          | 97.51 | 100.00 | 100.00 |      |       |       |       |       |



SEM HV: 10.00 kV    WD: 39.73 mm    VEGA\\ TESCAN  
 SEM MAG: 4.21 kx    Det: BSE    10 μm  
 Vac: HiVac    Date(m/d/y): 01/21/16    NEXT - LNF - INFN

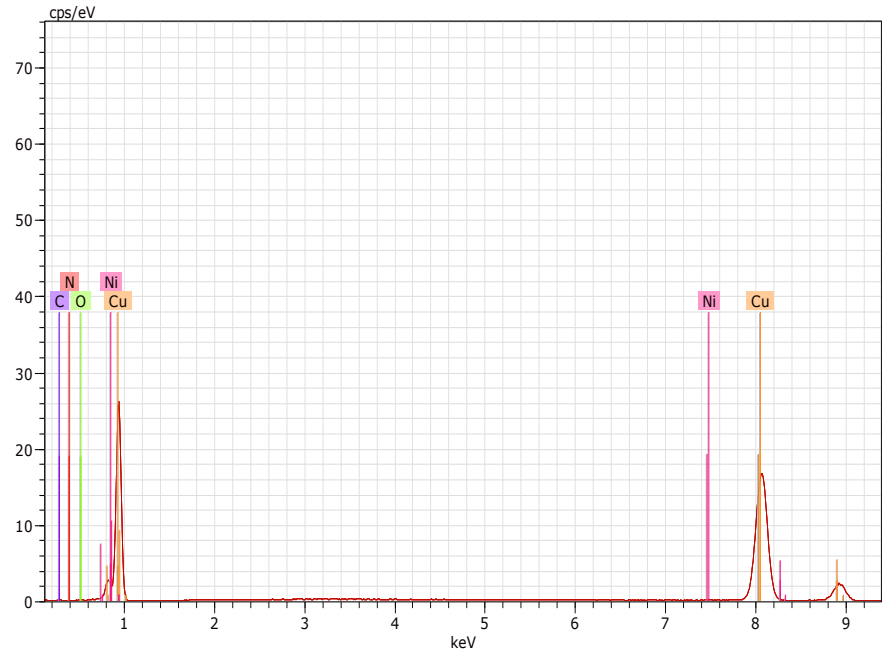
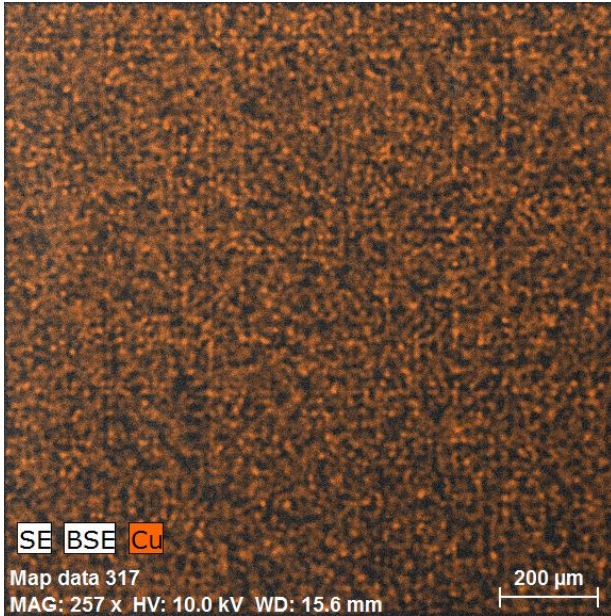


Spectrum: Acquisition 861-Generale.spx

| El | AN | Series | unn. [wt.%] | C norm. [wt.%] | C Atom. [at.%] | Error (1 Sigma) | K fact. | Z corr. | A corr. | F corr. |
|----|----|--------|-------------|----------------|----------------|-----------------|---------|---------|---------|---------|
|----|----|--------|-------------|----------------|----------------|-----------------|---------|---------|---------|---------|

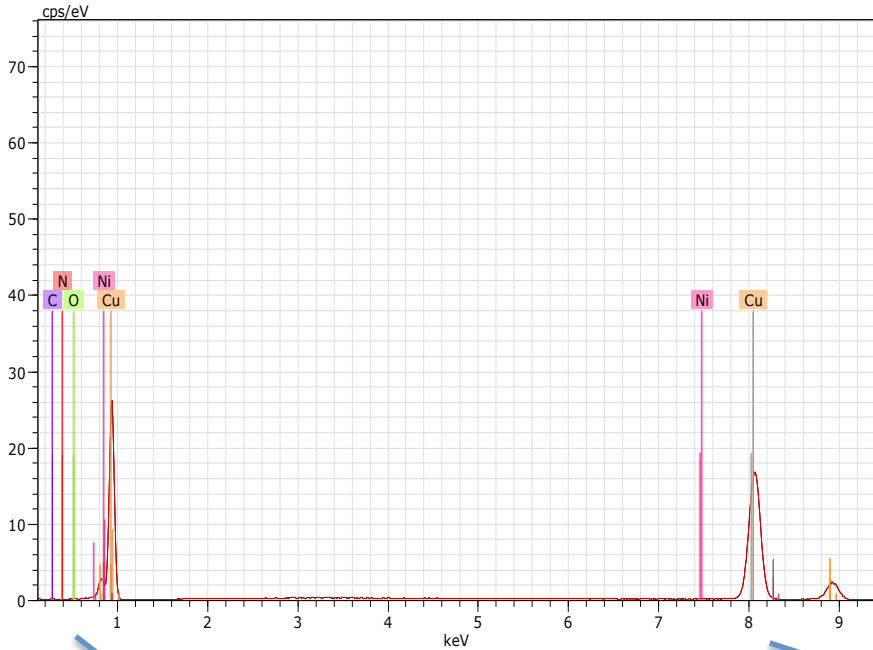
|    |    |          |       |       |       |  |      |       |       |       |       |
|----|----|----------|-------|-------|-------|--|------|-------|-------|-------|-------|
| Cu | 29 | K-series | 88.20 | 96.47 | 83.80 |  | 2.42 | 0.862 | 1.078 | 1.000 | 1.039 |
| C  | 6  | K-series | 3.22  | 3.53  | 16.20 |  | 0.86 | 0.091 | 0.387 | 1.000 | 1.000 |

Total: 91.43    100.00    100.00



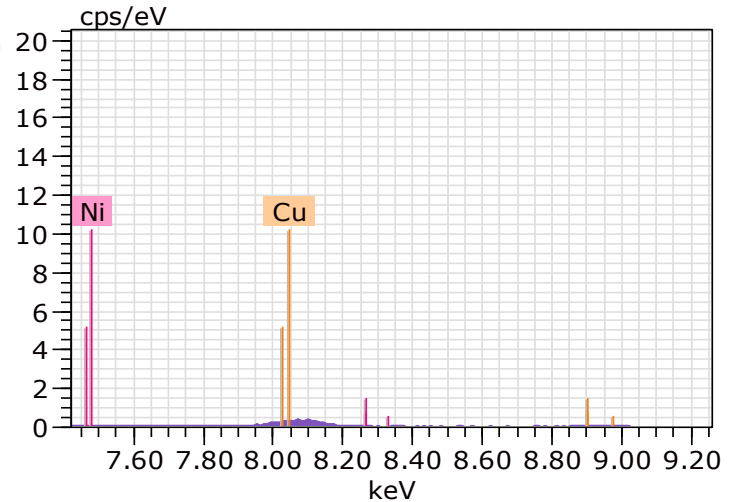
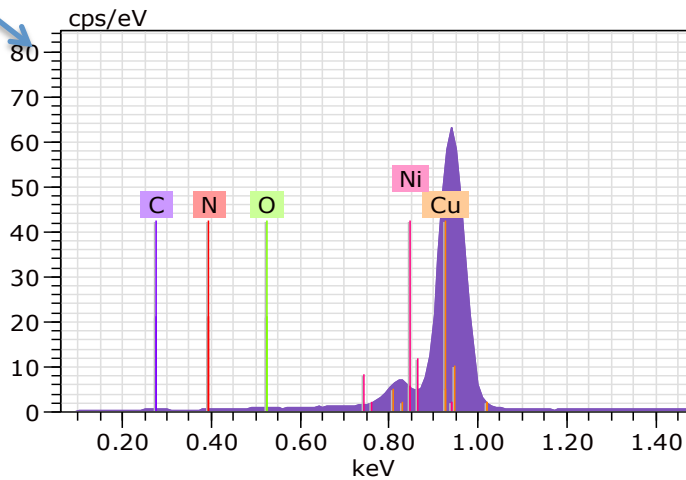
Spectrum: Acquisition 877

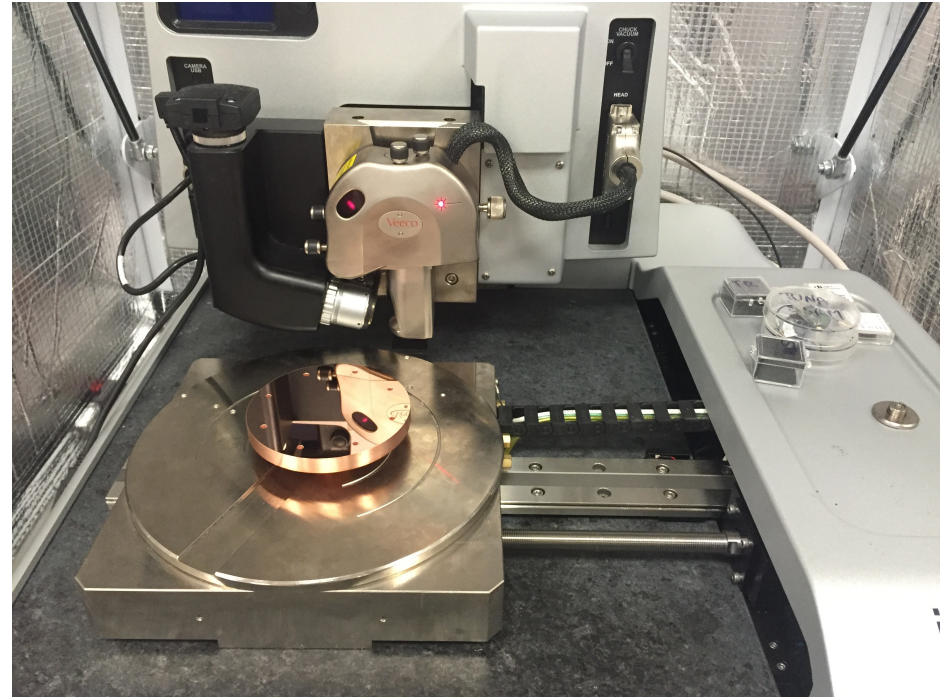
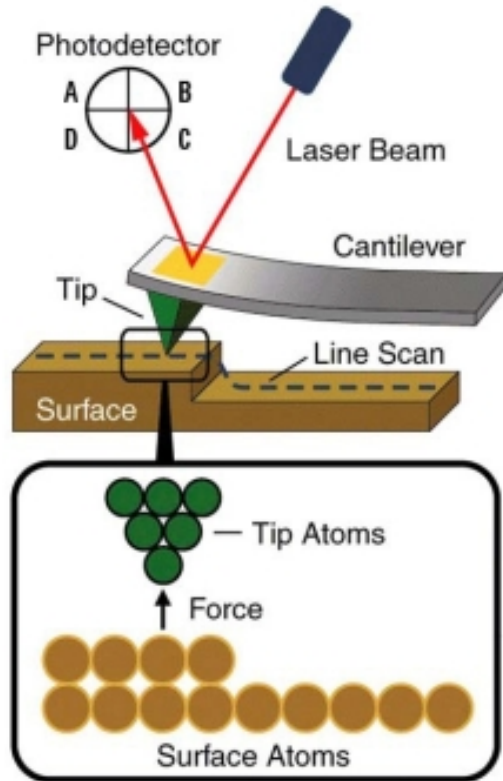
| El     | AN | Series   | Net unun. | C norm. | C Atom. | C Error (1 Sigma) |
|--------|----|----------|-----------|---------|---------|-------------------|
|        |    |          | [wt.%]    | [wt.%]  | [at.%]  | [wt.%]            |
| Cu     | 29 | L-series | 289089    | 98.81   | 98.81   | 10.64             |
| C      | 6  | K-series | 1280      | 0.47    | 2.39    | 0.12              |
| Ni     | 28 | L-series | 1453      | 0.34    | 0.35    | 0.09              |
| O      | 8  | K-series | 1150      | 0.22    | 0.86    | 0.07              |
| N      | 7  | K-series | 466       | 0.16    | 0.71    | 0.07              |
| Total: |    |          | 100.00    | 100.00  | 100.00  |                   |



Spectrum: Acquisition 877

| El     | AN | Series   | Net uncorr. | C norm. | C Atom. | C Error (1 Sigma) |
|--------|----|----------|-------------|---------|---------|-------------------|
|        |    |          | [wt.%]      | [wt.%]  | [at.%]  | [wt.%]            |
| -----  |    |          |             |         |         |                   |
| Cu     | 29 | L-series | 289089      | 98.81   | 98.81   | 10.64             |
| C      | 6  | K-series | 1280        | 0.47    | 0.47    | 0.12              |
| Ni     | 28 | L-series | 1453        | 0.34    | 0.34    | 0.09              |
| O      | 8  | K-series | 1150        | 0.22    | 0.22    | 0.07              |
| N      | 7  | K-series | 466         | 0.16    | 0.16    | 0.07              |
| -----  |    |          |             |         |         |                   |
| Total: |    |          | 100.00      | 100.00  | 100.00  |                   |





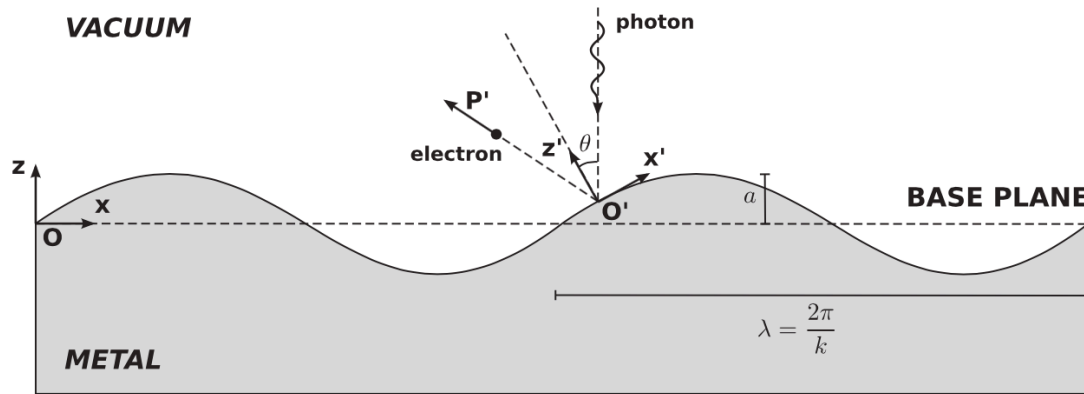
The surface roughness is represented by

$$R_a = (1/L) \int_0^L |Z(x)| dx$$

$$RMS(R_q) = \left[ (1/L) \int_0^L Z(x)^2 dx \right]^{1/2}$$

L, evaluation length  
Z(x), the profile height function

- **Surface roughness** on cathode introduces a transverse electric field that increases the transverse momentum, causing **emittance growth**.

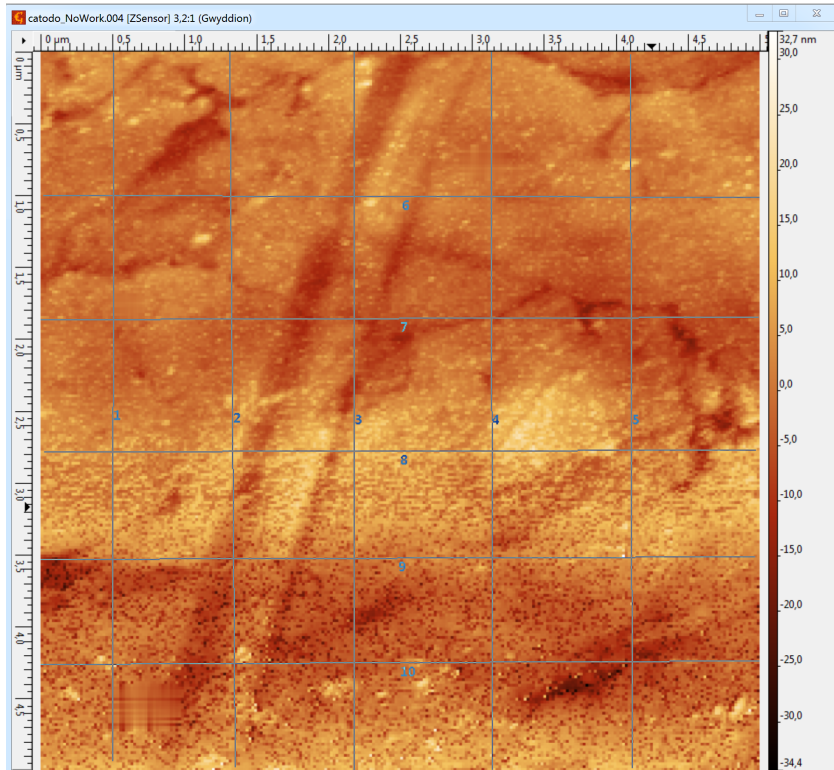


- $z = a \cos((2\pi/\lambda)x)$ , surface morphology function
- $a$ , amplitude of the uneven surface
- $\lambda$ , period of fluctuation

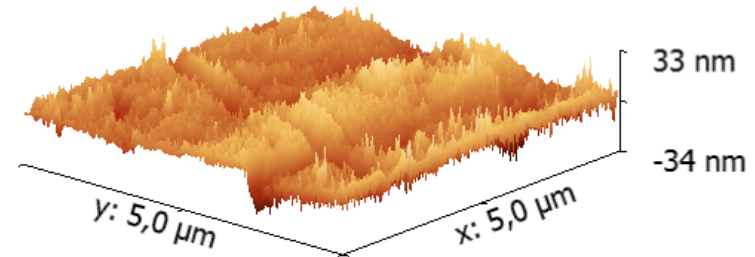
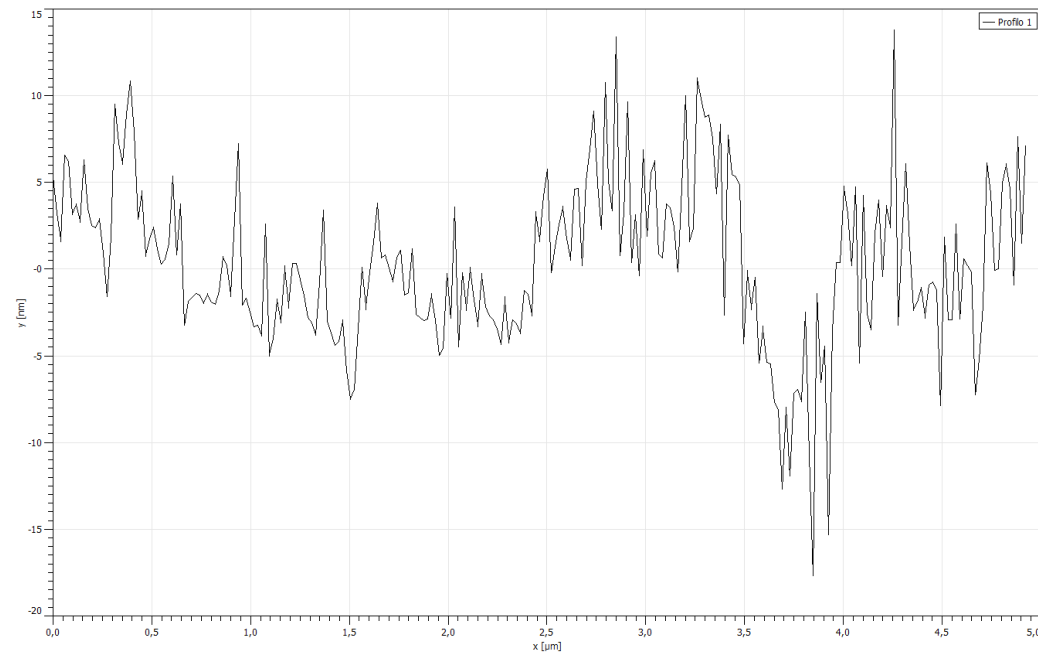
$$\varepsilon_{ns} = \sigma_x \sqrt{\frac{e\pi^2 a^2 E_{rf} \sin\vartheta_{rf}}{2m_0 c^2 \lambda}}$$

Z. Zhang and C. Tang, *Analytical study on emittance growth caused by roughness of a metallic photocathode*, PRST-AB 18, 053401 (2015)

D. Xiang et al., *First principle measurements of thermal emittance for copper and magnesium*, Proc. of PAC07, Albuquerque, New Mexico, USA



## Profile of image



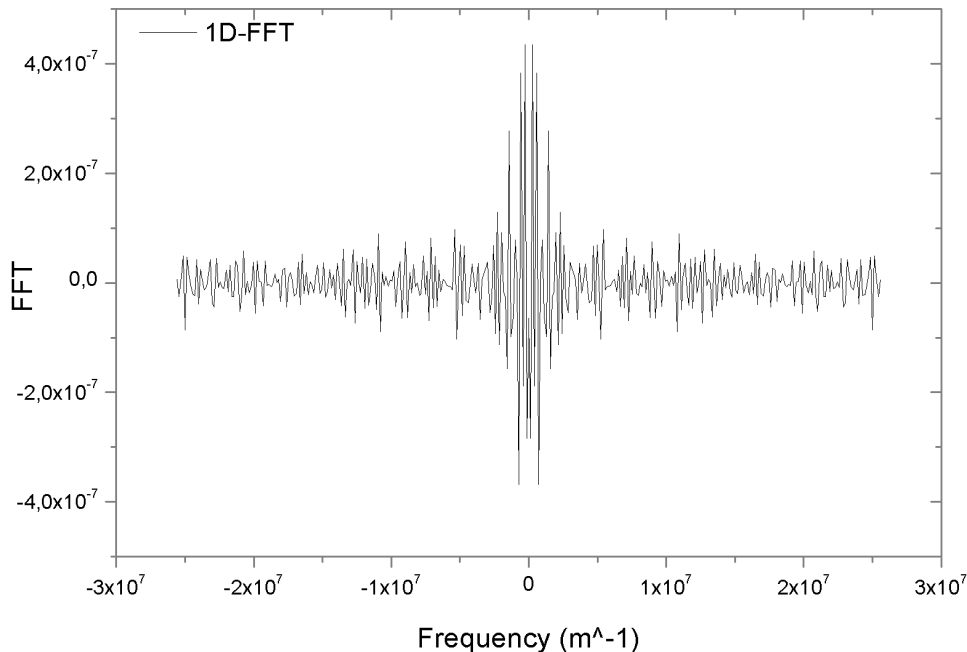
### Statistical parameters:

|            |          |
|------------|----------|
| Min_value: | -34,4 nm |
| Max_value: | 32,6 nm  |
| Ra (Sa):   | 4,3 nm   |
| Rms (Sq):  | 5,7 nm   |

# Fourier transform of AFM image

$$\text{Re} \{F[l]\} = \frac{1}{N} \sum_{n=0}^{N-1} \text{Re} \{f[n]\} \cos 2\pi \frac{n}{N} l$$

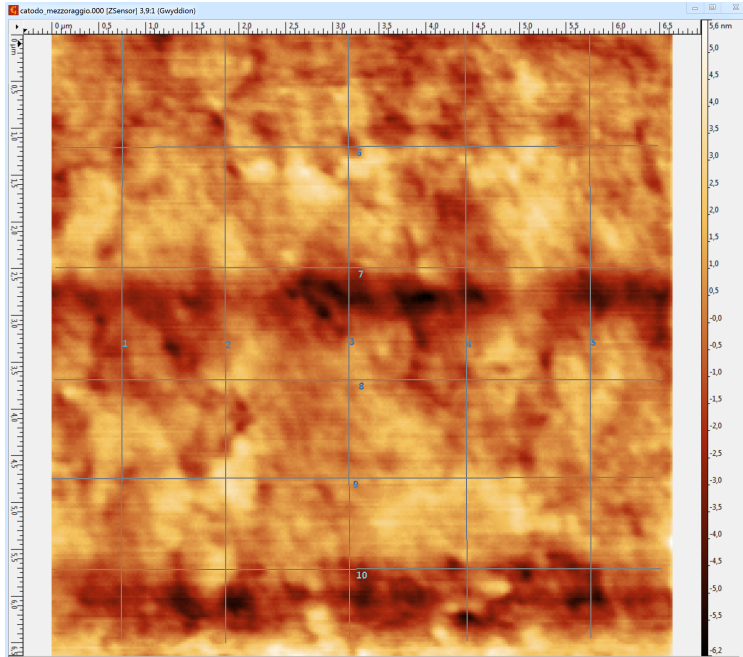
1D-DFT



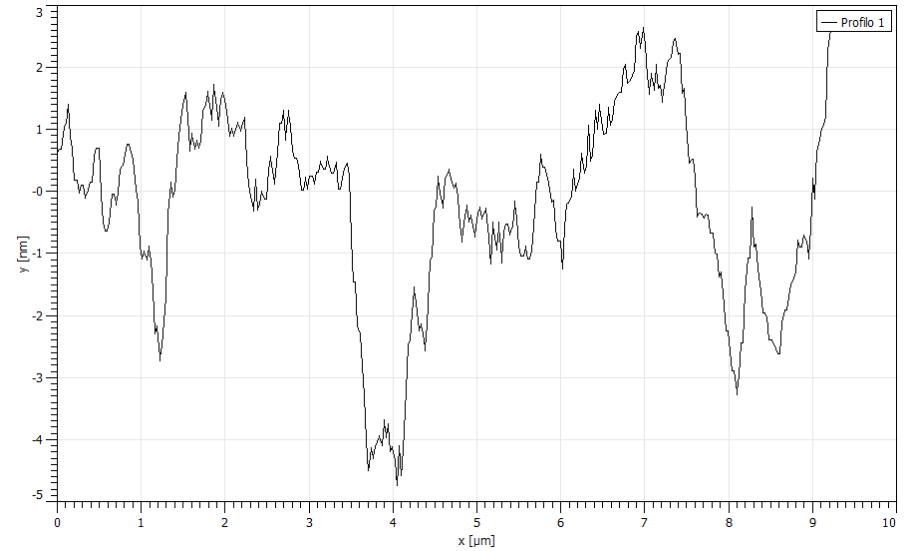
$$\left[ \begin{array}{l} a_n = \text{Re} \{f[n]\} \\ \lambda_n = \frac{L_{cathode}}{n} \end{array} \right]$$

$$\sum_{n=0}^{N-1} \frac{a_n^2}{\lambda_n} = \underline{\underline{3.13e - 11m}}$$



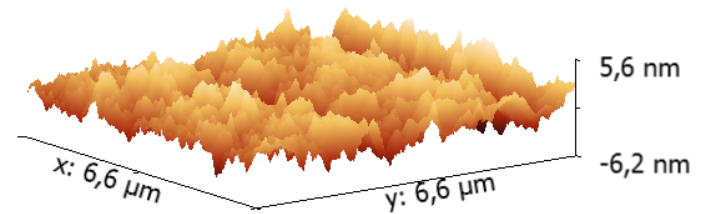


## Profile of image



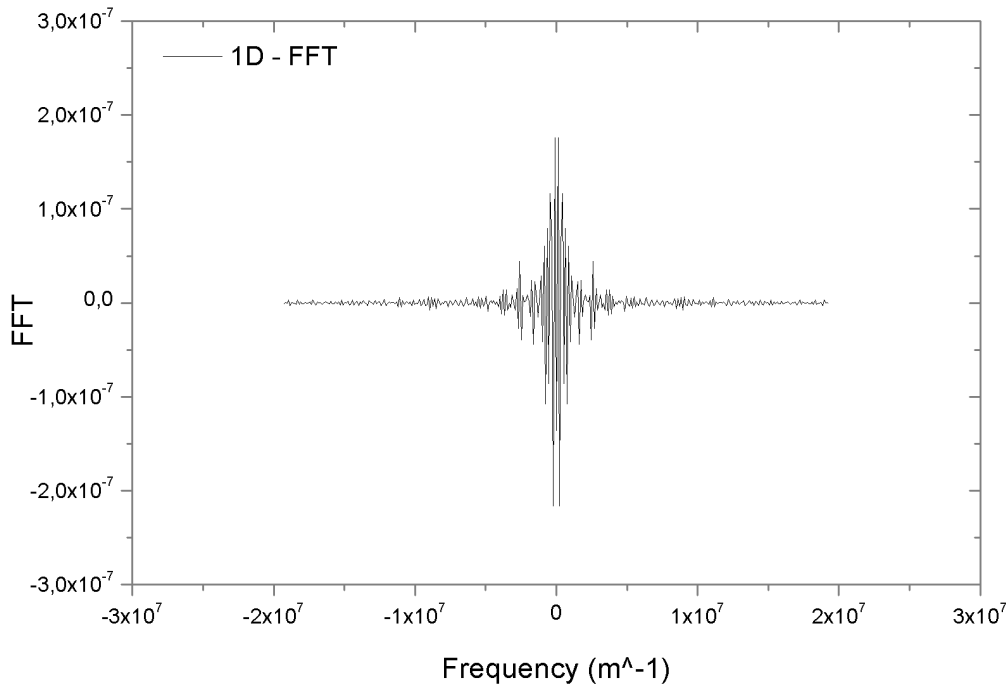
Statistical parameters:

|            |          |
|------------|----------|
| Min_value: | -6,16 nm |
| Max_value: | 5,60 nm  |
| Ra (Sa):   | 1,18 nm  |
| Rms (Sq):  | 1,501 nm |



# Fourier transform of AFM image

$$Re \{F[l]\} = \frac{1}{N} \sum_{n=0}^{N-1} Re \{f[n]\} \cos 2\pi \frac{n}{N} l \quad \underline{\underline{1D-DFT}}$$



$$\left[ \begin{array}{l} a_n = Re \{f[n]\} \\ \lambda_n = \frac{L_{cathode}}{n} \end{array} \right]$$

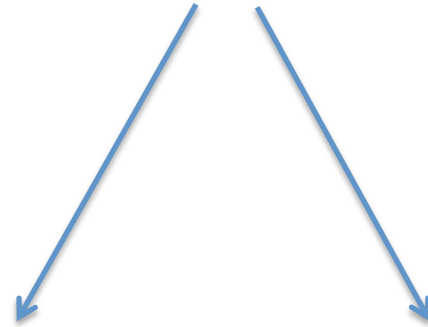
$$\sum_{n=0}^{N-1} \frac{a_n^2}{\lambda_n} = \underline{\underline{4e - 13m}}$$

$$\epsilon_{total}^2 = \sum_{n=0}^{N-1} \epsilon^2(a_n, k_n) = \sigma_x^2 \frac{\pi^2 e E_{rf} \sin \theta_{rf}}{2mc^2} \sum_{n=0}^{N-1} \frac{a_n^2}{\lambda_n}$$

$$E_{rf} = 97 \text{ MV} / \text{m}$$

$$\theta_{rf} = 30^\circ$$

$$\sigma_x = 0.3 \text{ mm}$$



**Before n-machining**

$$\sum_{n=0}^{N-1} \frac{a_n^2}{\lambda_n} = 3.13e - 11 \text{ m}$$

$$\sqrt{\epsilon_{total}^2} = 0.04 \mu\text{m}$$

**After n-machining**

$$\sum_{n=0}^{N-1} \frac{a_n^2}{\lambda_n} = 4e - 13 \text{ m}$$

$$\sqrt{\epsilon_{total}^2} = 0.004 \mu\text{m}$$

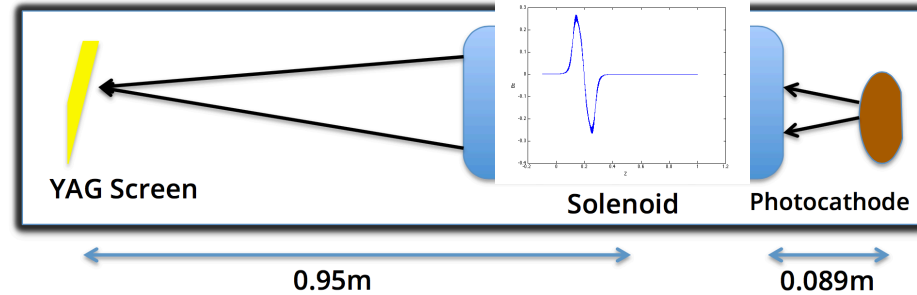
# Emittance measurements: experimental set up

- Photocathode laser

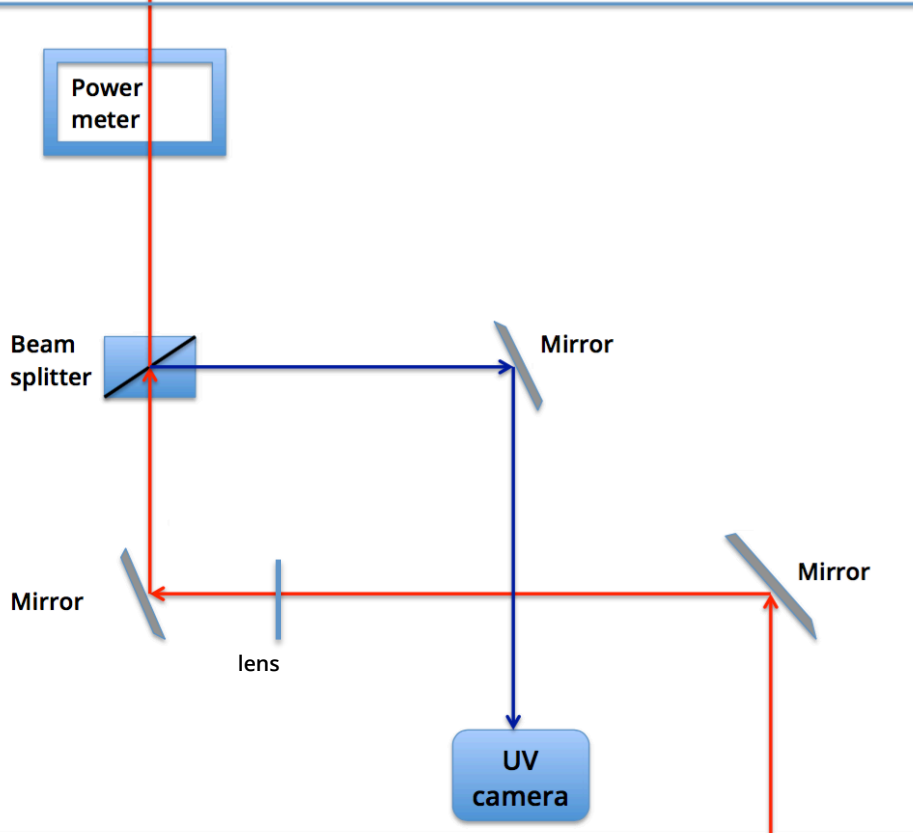
Beam line



- Beam line



**Solenoid is in not-rotating configuration, that is no x/y coupling**



## Solenoid Scan Technique:

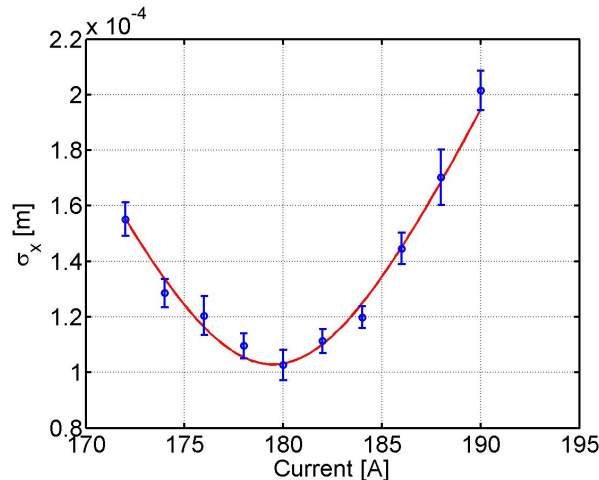
1. Measure of beam size squared on YAG Screen for different solenoid field is given by:

$$\langle x_i \rangle^2 = R_{11}^{(i)2} \langle x_0^2 \rangle + 2R_{11}^{(i)}R_{12}^{(i)} \langle x_0 x_0' \rangle + R_{12}^{(i)2} \langle x_0'^2 \rangle$$

Where the coefficients  $R_{11}$  and  $R_{12}$  are the elements of beam line transfer matrix.

2. Total normalized emittance has been computed at the entrance of gun solenoid:

$$\epsilon_{nx,rms} = \gamma\beta\sqrt{\langle x_0^2 \rangle \langle x_0'^2 \rangle - \langle x_0 x_0' \rangle^2}$$



At the entrance of gun solenoid:

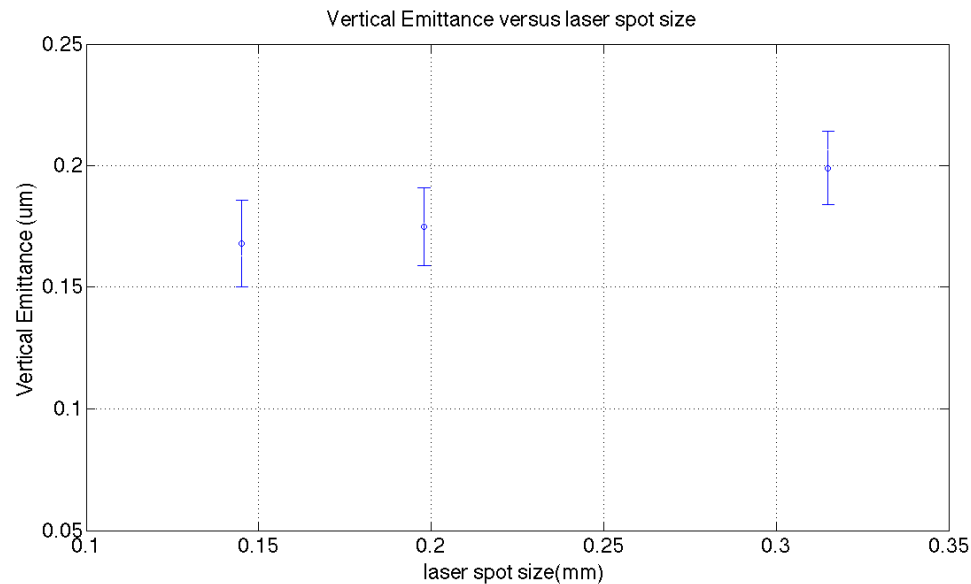
$$\epsilon_{nx} = 0.16 \pm 0.01 \text{ mmmrad}$$

$$\beta x_{in} = 0.38 \pm 0.04 \text{ m}$$

$$\alpha x_{in} = -6.8 \pm 0.8$$

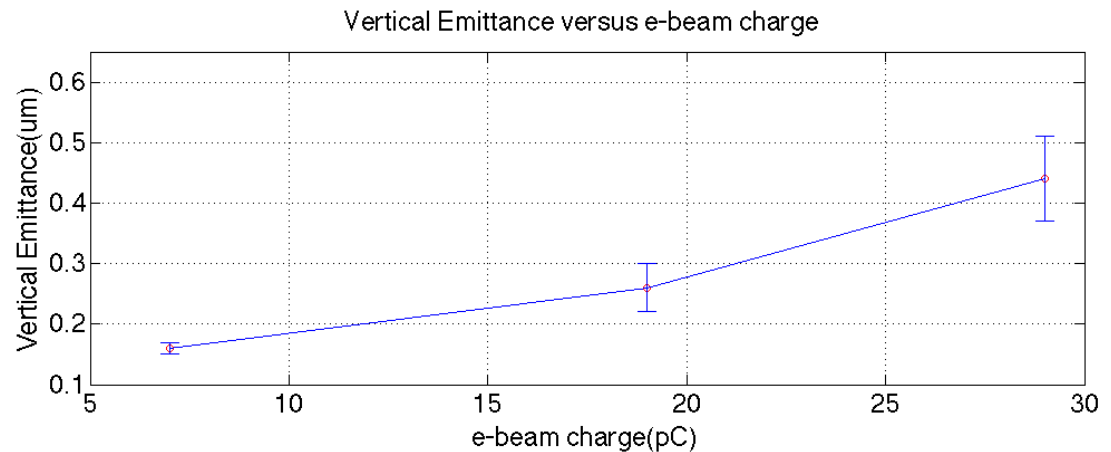
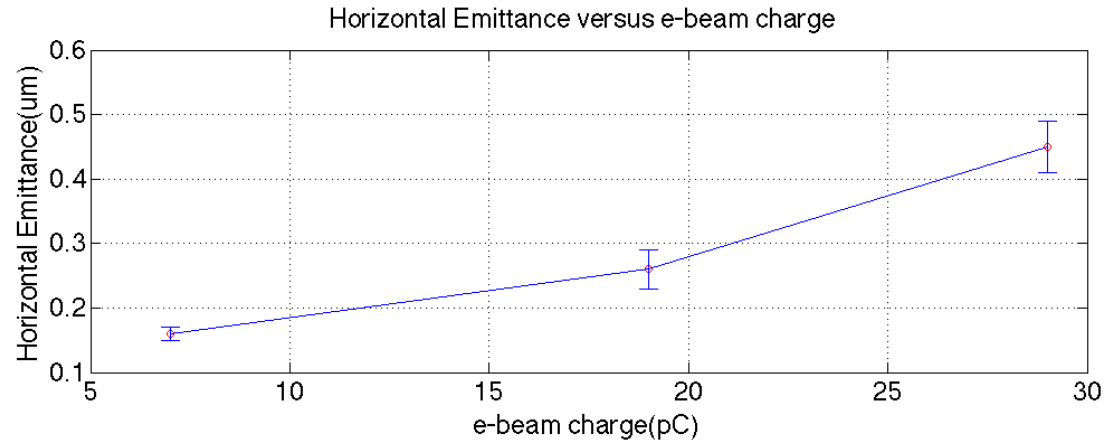
**Parameters:**

- $E_{\text{peak}} = 84 \text{ MV/m}$
- Working RF phase =  $30^\circ$
- Laser pulse length = 5 ps - FWHM (Gaussian profile)
- $E = 4.01 \pm 0.05 \text{ MeV}$  - Energy at the gun exit
- Bunch charge  $\cong 6 \text{ pC}$



## Parameters:

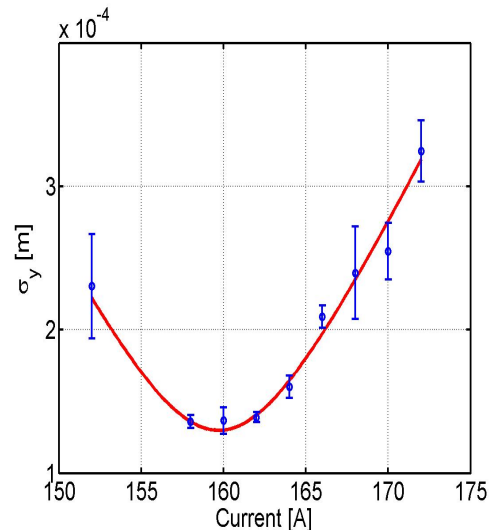
- Epeak= 97MV/m
- Working RF phase=30°
- Laser pulse length =5ps - FWHM (Gaussian profile)
- E= 4.53±0.05MeV - Energy at the gun exit
- $\sigma_{x,y,rms}$  (Laser spot)≈0.3mm (Flat top profile)



## Before n-machining

### Parameters:

- $E_{peak} = 84 \text{ MV/m}$
- Working RF phase =  $30^\circ$
- Laser pulse length =  $5 \text{ ps}$  - FWHM (Gaussian profile)
- $E = 4.01 \pm 0.05 \text{ MeV}$  - Energy at the gun exit
- Bunch charge  $\cong 6 \text{ pC}$



At the entrance of gun solenoid:

$$\varepsilon_{nx} = 0.28 \pm 0.04 \text{ mmmrad}$$

$$\beta x_{in} = 0.42 \pm 0.06 \text{ m}$$

$$\alpha x_{in} = -7.33 \pm 0.13$$



# Emittance measurements before and after n-machining

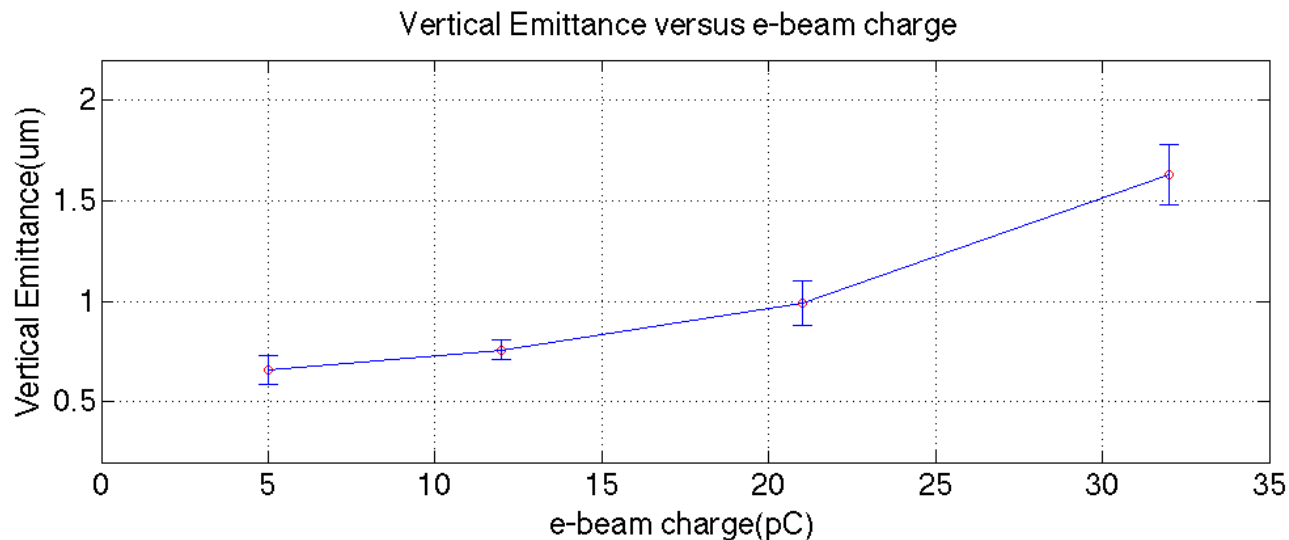
**Parameters:**

- $E_{\text{peak}} = 84 \text{ MV/m}$
- Working RF phase =  $30^\circ$
- Longitudinal length laser beam = 5ps - FWHM (Gaussian profile)
- Bunch charge  $\approx 6 \text{ pC}$

|                         | <i>Before n-machining</i> |                       | <i>After n-machining</i> |                       |
|-------------------------|---------------------------|-----------------------|--------------------------|-----------------------|
| $E_{\text{acc}}$ (MV/m) | $\epsilon_x$ (mmmrad)     | $\epsilon_y$ (mmmrad) | $\epsilon_x$ (mmmrad)    | $\epsilon_y$ (mmmrad) |
| 84                      | $0.24 \pm 0.04$           | $0.28 \pm 0.04$       | $0.105 \pm 0.012$        | $0.114 \pm 0.010$     |

## Parameters:

- E<sub>peak</sub>= 110MV/m
- Working RF phase=30°
- Laser pulse length =5.3ps - FWHM (Gaussian profile)
- E= 4.66MeV - Energy at the gun exit
- $\sigma_{x,yrms}$  (Laser spot)≅0.11mm (Gaussianprofile)



- For our applications the **dry machining** is a good procedure because we don't have residual of diamond paste or oil
- We obtain an excellent roughness ( $\leq 2\text{nm}$ ) typical of monocrystalline copper cathode
- With the n-machining we improved of a factor **2** the total beam emittance

- ✧ D. Alesini, M.P. Anania, M. Bellaveglia, S. Bellucci, A. Biagioni, F. Bisesto, F. Cardelli, E. Chiadroni, G. Costa, D. Di Giovenale, G. Di Pirro, R. Di Raddo, A. Giribono, M. Ferrario, F. Micciulla, R. Pompili, L. Piersanti, V. Shpakov, A. Stella, F. Villa (INFN-LNF)
- ✧ A. Cianchi (INFN-Roma Tor Vergata and Università di Roma “Tor Vergata”)
- ✧ Andrea Mostacci, Daniele Passeri (SBAI- Università di Roma “La Sapienza”)
- ✧ A. Lorusso (Università del Salento, Dipartimento di Matematica e Fisica “E. De Giorgi”, INFN-Sezione di Lecce)
- ✧ Mauro Trovò (Elettra - Sincrotrone Trieste SCpA )



Finally it's over



***Thank you for your attention***